



Silicon Photomultiplier (SiPM): a flexible platform for the development of high-end instrumentation

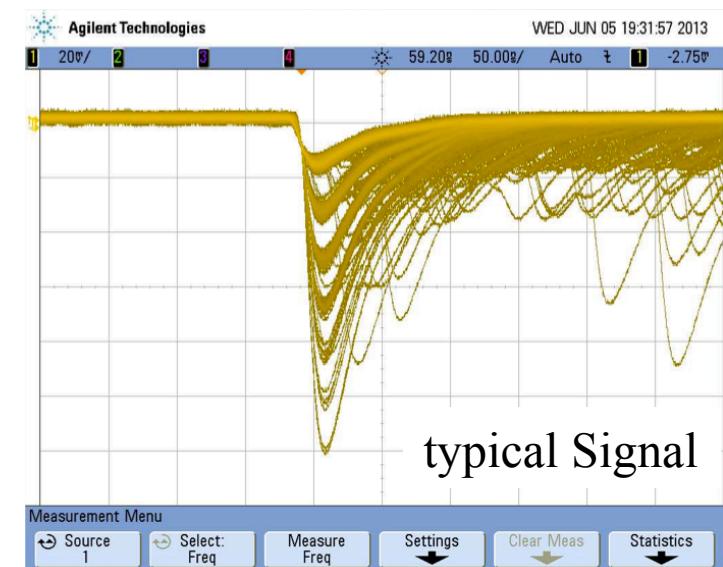
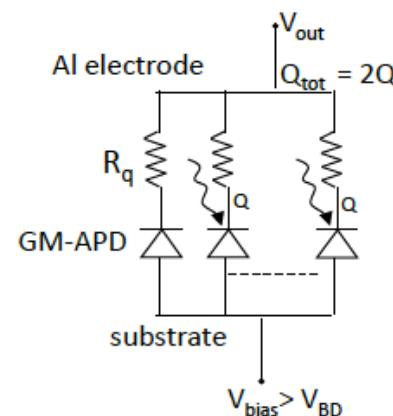
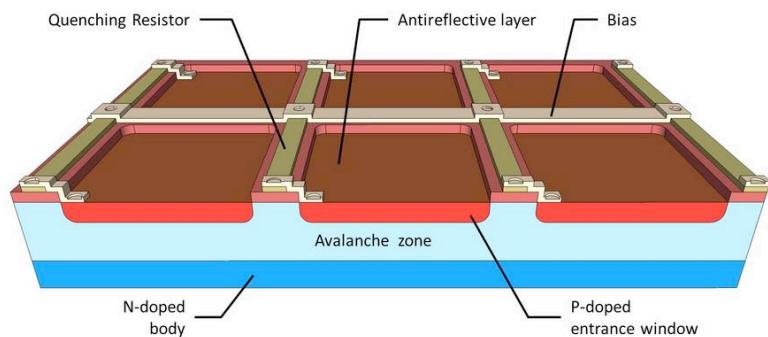
Romualdo Santoro* and M. Caccia
Università dell'Insubria, Como (Italy)



Photons detectors: SiPM

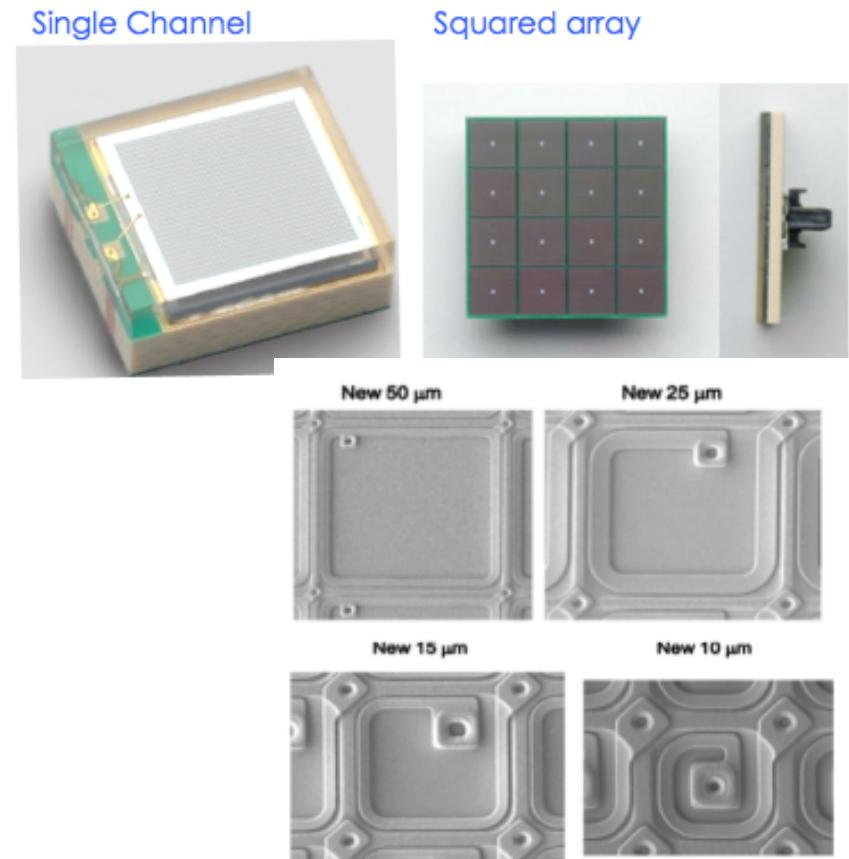
- ▶ SiPM is a High density (up to $10^4/\text{mm}^2$) matrix of diodes with a common output, working in Geiger-Müller regime
- ▶ Common bias is applied to all cells (few % over breakdown voltage)
- ▶ Each cell has its own quenching resistor (from $100\text{k}\Omega$ to several $\text{M}\Omega$)
- ▶ When a cell is fired an avalanche starts with a multiplicative factor of about $10^5\text{-}10^6$
- ▶ The output is a fast signal ($t_{\text{rise}} \sim \text{ns}$; $t_{\text{fall}} \sim 50 \text{ ns}$) sum of signals produced by individual cells
- ▶ SiPM works as an analog photon detector: signal proportional to the number of fired cell

SiPM: Basic principle



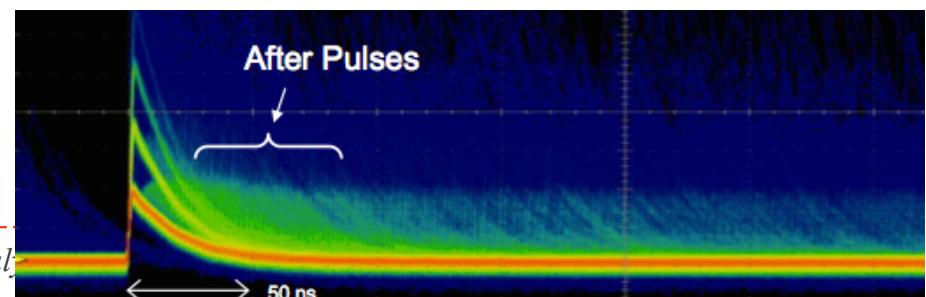
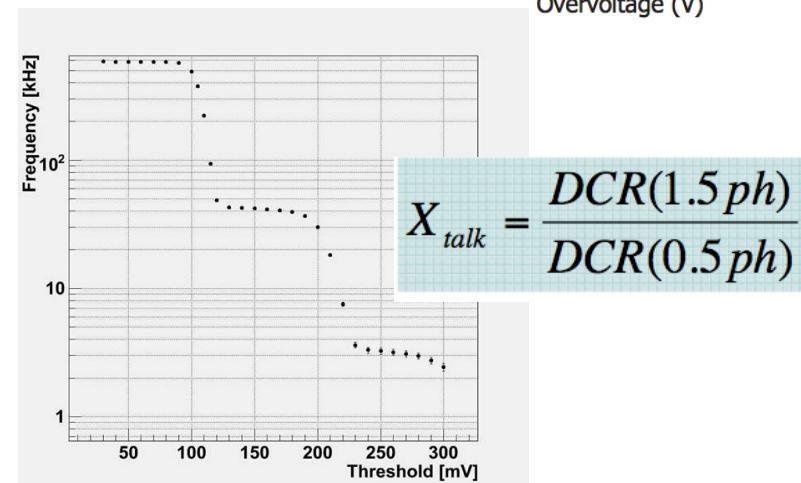
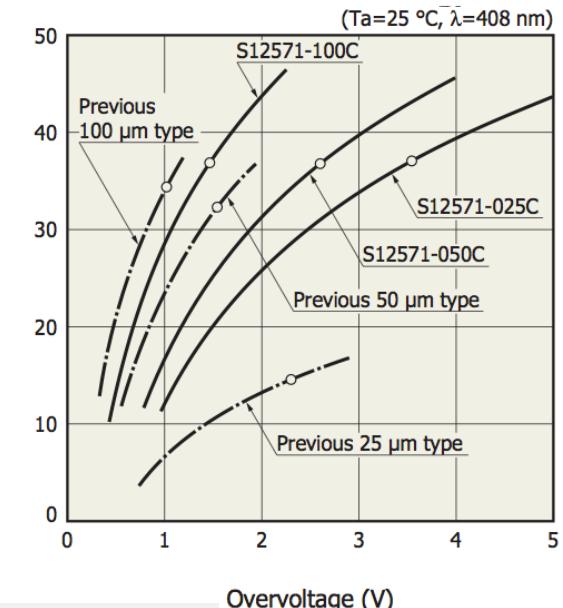
Wide range of products

- ▶ Different geometry
 - ▶ single chip (i.e. 1x1, 3x3 and 6x6 mm²)
 - ▶ array: (i.e. linear or squared) with common or separate output
- ▶ Different Fill factor
 - ▶ Pixel size (from 10 to 100 µm)
 - ▶ different technology (with/witout trenches)



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 - ▶ Pixel size (from 10 to 100 µm)
 - ▶ different technology (with/witout trenches)
- ▶ Long list of parameters to be measured
 - ▶ QE, PDE
 - ▶ Gain vs voltage and temperature
 - ▶ DCR, After pulse and cross-talk
 - ▶ time resolution
 - ▶ ...



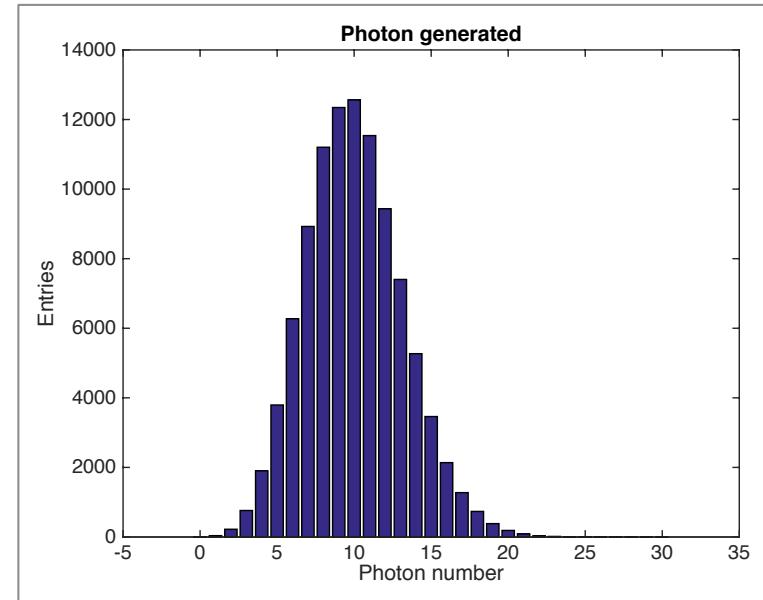
Why a fast simulation could be of interest?

- ▶ To reproduce the typical measurements done in the lab and to better understand the results especially when:
 - ▶ you characterize new sensors
 - ▶ you define new protocols
- ▶ To investigate new applications trying to better identify the sensor requirements

*By the way, it isn't the real world!
There are a series of assumptions and
measurements to be done on SiPMs*

Simulation block diagram

1. Light (poissonian statistics)

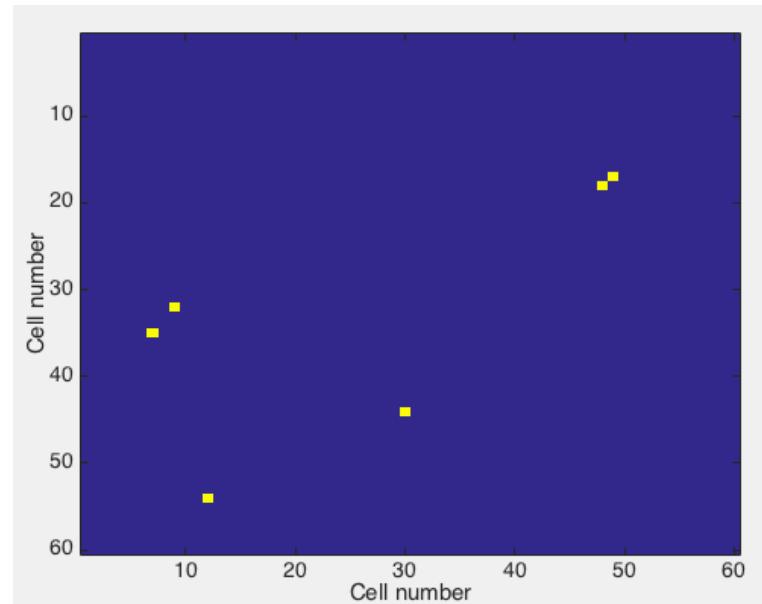


Simulation Parameters:

- ▶ Event = 10^5
- ▶ $\mu = 10$ Photons

Simulation block diagram

1. Light (poissonian statistics)
2. Detector characteristics:
number of pixel, eff, Xtalk

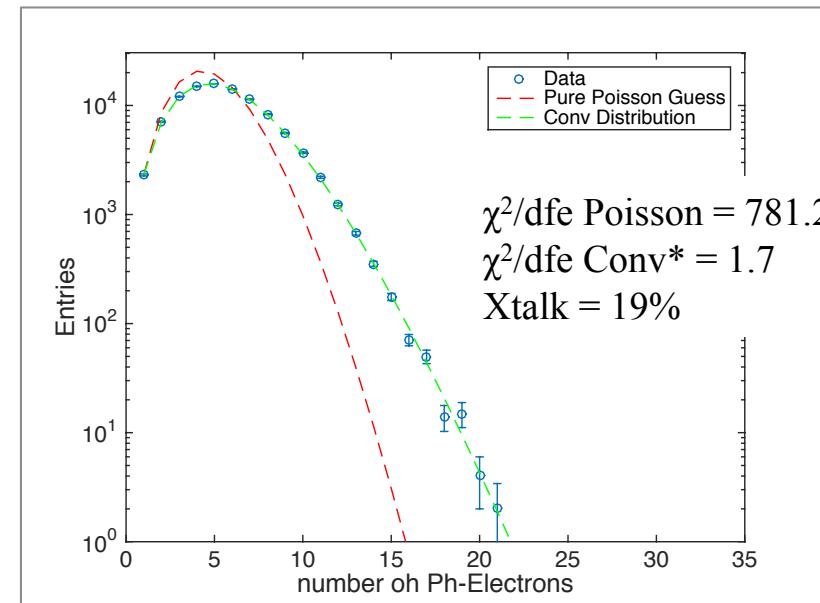


Simulation Parameters:

- ▶ number of cells = 3600
- ▶ eff = 38%
- ▶ Xtalk = 20%

Simulation block diagram

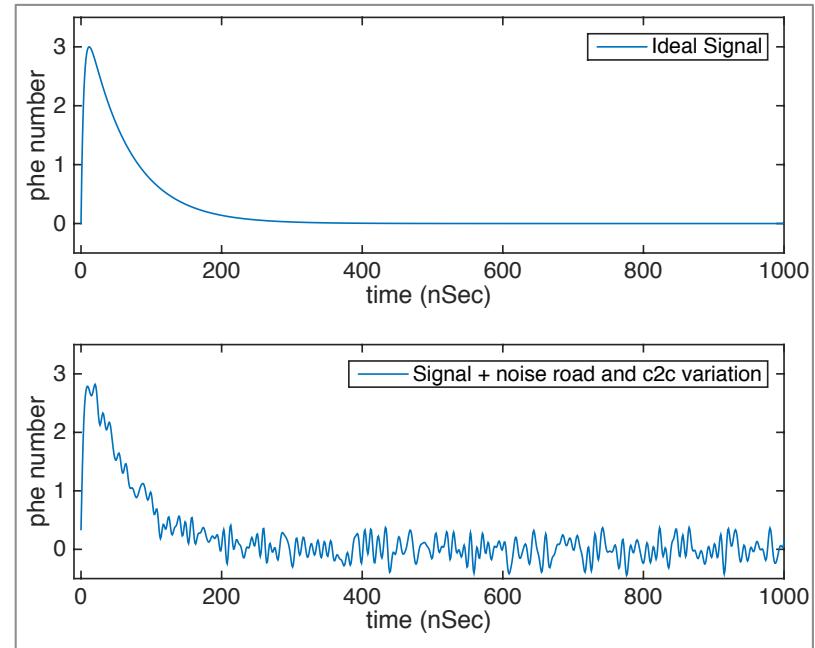
1. Light (poissonian statistics)
2. Detector characteristics:
number of pixel, eff, Xtalk
3. Number of pixel Hit due to
Phe and Xtalk



*Conv = S. Vinogradov et al. (NSS/MIC), 2009 IEEE
This fit nicely but I could also try the N.Borel (Erlang)
see Thomas Bretz talk at this conference

Simulation block diagram

1. Light (poissonian statistics)
2. Detector characteristics:
number of pixel, eff, Xtalk
3. Number of pixel Hit due to
Phe and Xtalk
4. Signal characteristics:
signal tau, noise and
cell2cell variation

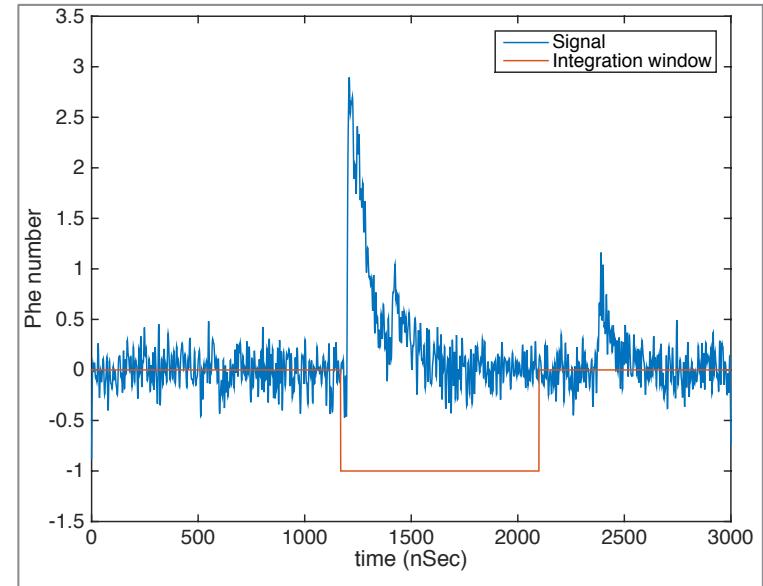


Simulation Parameters:

- ▶ $\tau_{\text{signal}}=60\text{nSec}$
- ▶ Cell2Cell Variation=0.1phe
- ▶ SNR=10

Simulation block diagram

1. Light (poissonian statistics)
2. Detector characteristics:
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signal tau, noise and
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5. DCR and AfterPuls +
correlated xTalk



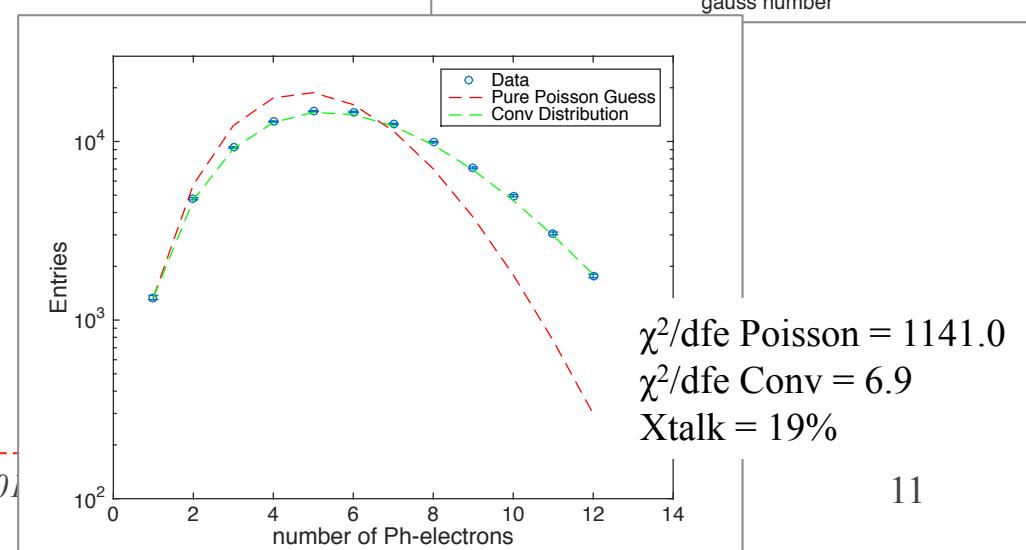
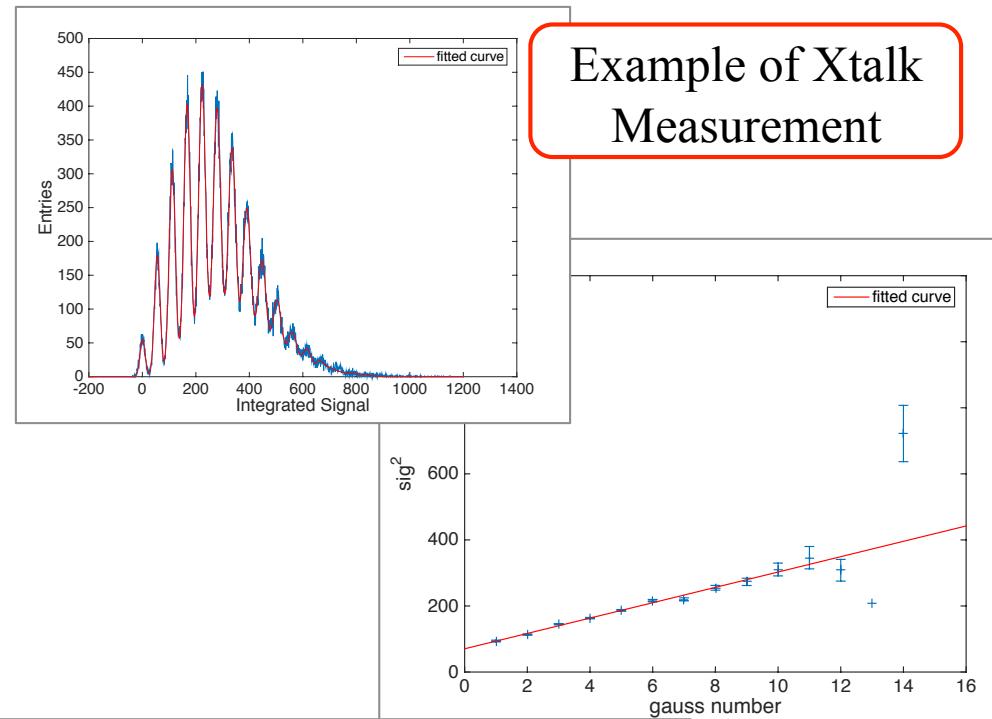
Simulation Parameters:

- ▶ DCR=300 kHz
- ▶ Xtalk=20%
- ▶ AfterPulse (AP)=20%
- ▶ τ_{AP} =80 (slow) and 15 (fast) @ 50% ratio

Simulation block diagram

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6. Analysis tool

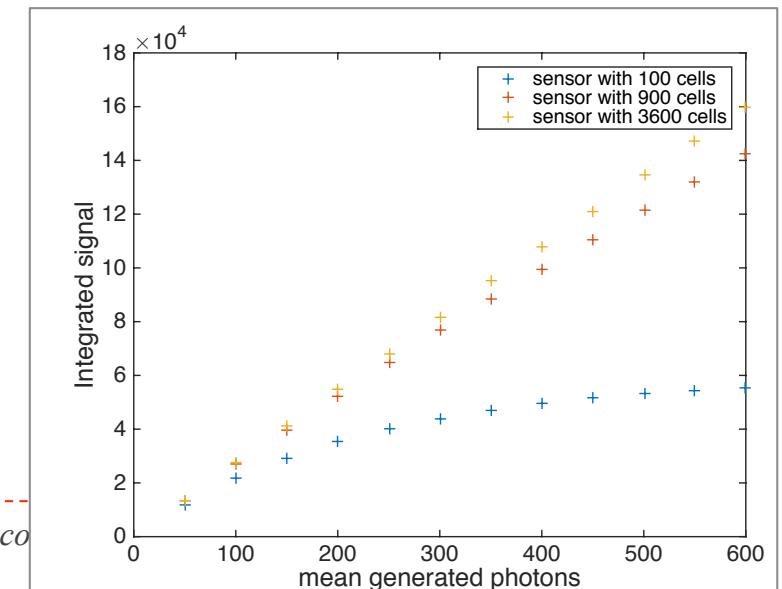
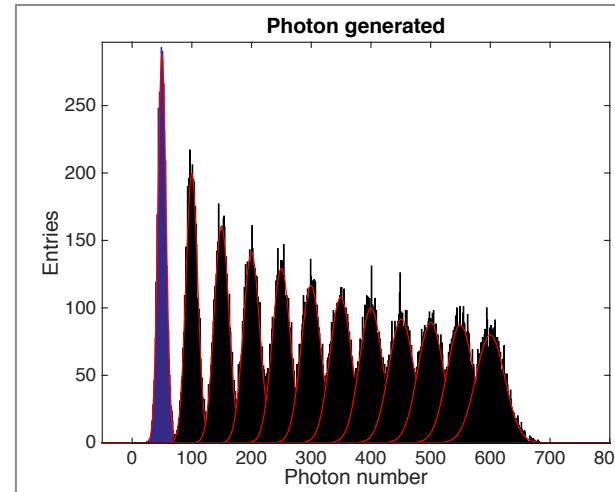
Example of Xtalk
Measurement



Simulation block diagram

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Phe and Xtalk
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Example of light saturation Measurement



SiPM for homeland security

- ▶ MODES_SNM has been founded by the European Commission within the Framework Program 7
- ▶ The Main Goal is the development of a system with detection capabilities of “**difficult to detect radioactive sources and special nuclear materials**”
 - ▶ Neutron detection with high γ rejection power
 - ▶ γ -rays spectrometry
- ▶ Other requirements
 - ▶ Mobile system
 - ▶ Scalability and flexibility to match a specific monitoring scenario
 - ▶ Remote control, to be used in covert operations

modes SNM

Modular Detector System for Special Nuclear Material



Two main Goals

- ▶ The demonstrator: a fully integrated system based on high pressure scintillating gas readout by PMT
 - ▶ Fast neutron (^4He)
 - ▶ Thermal neutron (^4He with Li converter)
 - ▶ Gamma (Xe)
- ▶ The proof of principle of PMT replacement with the innovative SiPM



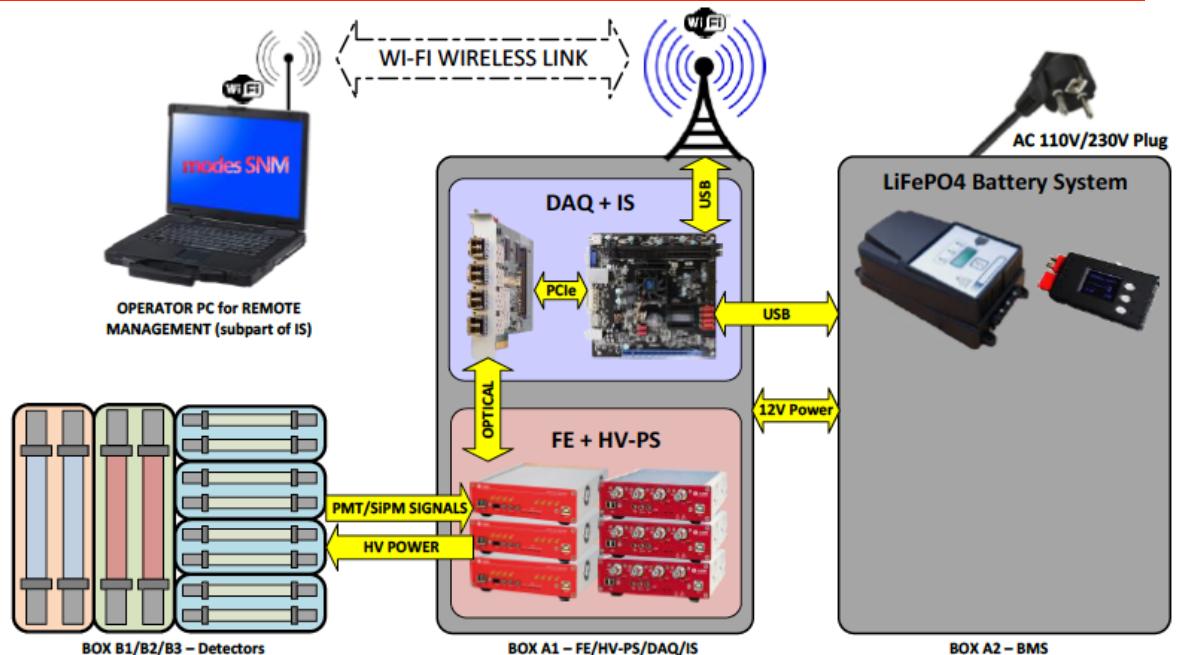
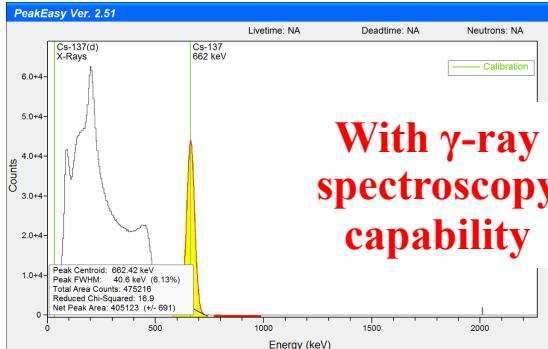
Available on the market:

[http://www.arktis-detectors.com/
products/security-solutions/](http://www.arktis-detectors.com/products/security-solutions/)



Now prototyped by Arktis and shown at NSS/MIC 2014 at Seattle

MODES_SNM System overview



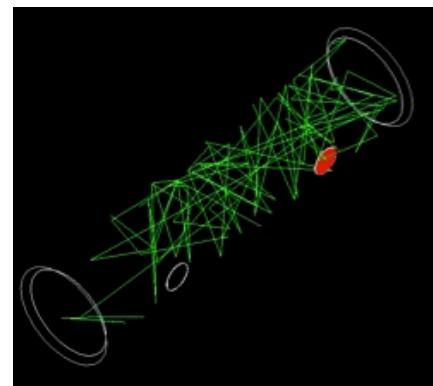
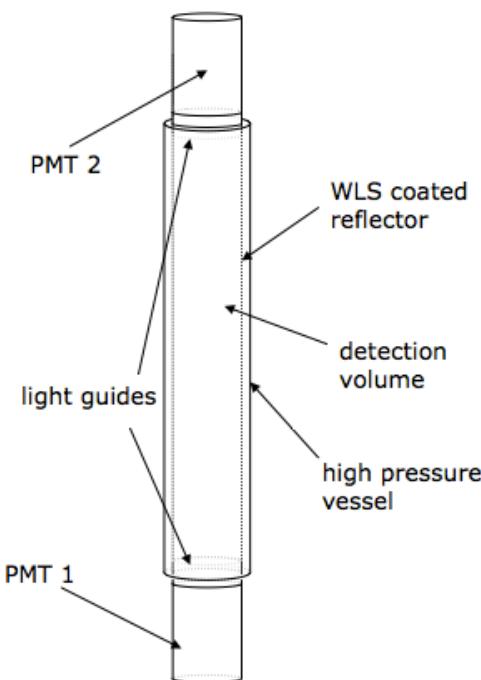
Modular system optimized for:

- ▶ Fast neutron (^4He)
- ▶ Thermal neutron (^4He with Li converter)
- ▶ Gamma (Xe)

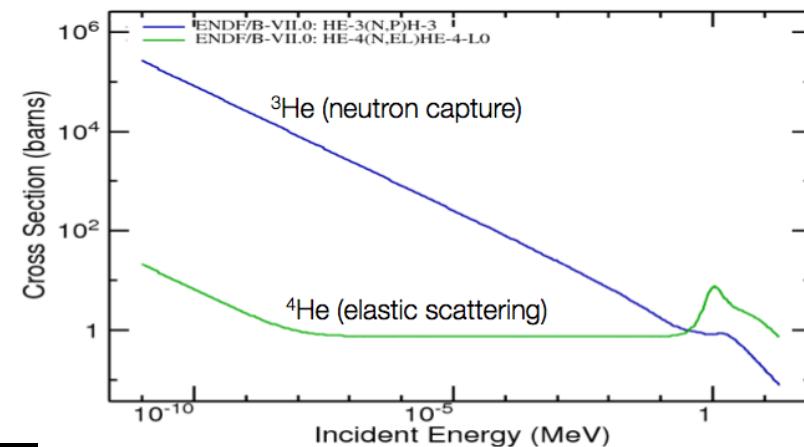


Baseline technology

- ▶ The Arktis technologies is based on high pressurized ^4He for the neutrons detection
- ▶ The main key features of ^4He
 - ▶ Reasonably high cross section for n elastic scattering
 - ▶ Good scintillating properties
 - ▶ Two component decays, with τ at the ns and μs levels
 - ▶ Cheaper and easier to be procured wrt ^3He



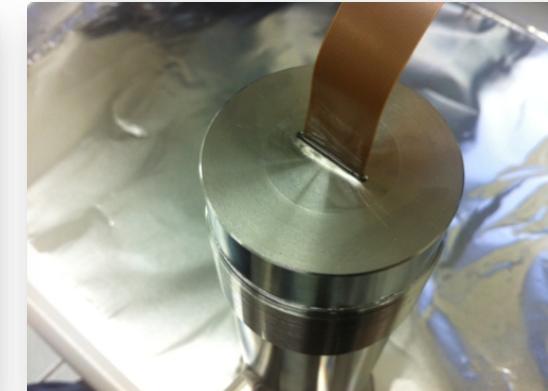
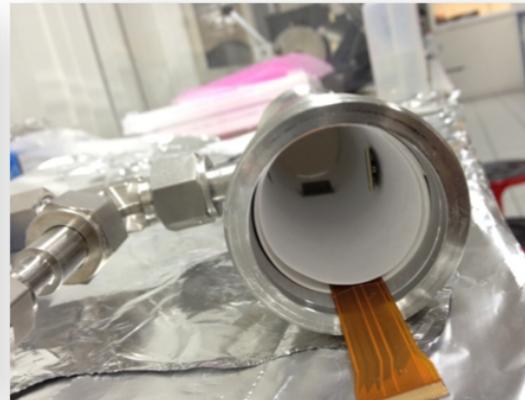
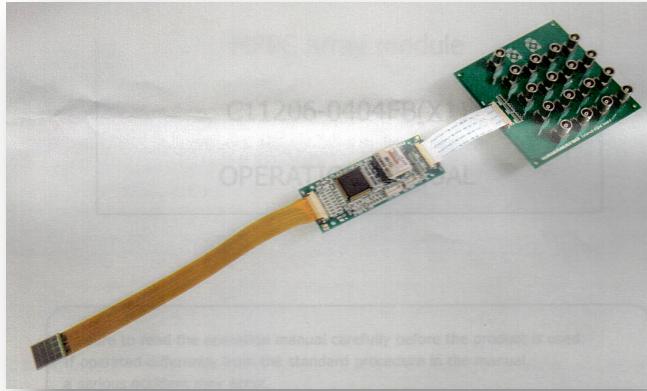
- ▶ 4.4 cm diameter x 47 cm sensitive length
- ▶ 180 bar ^4He sealed system maintaining gas purity



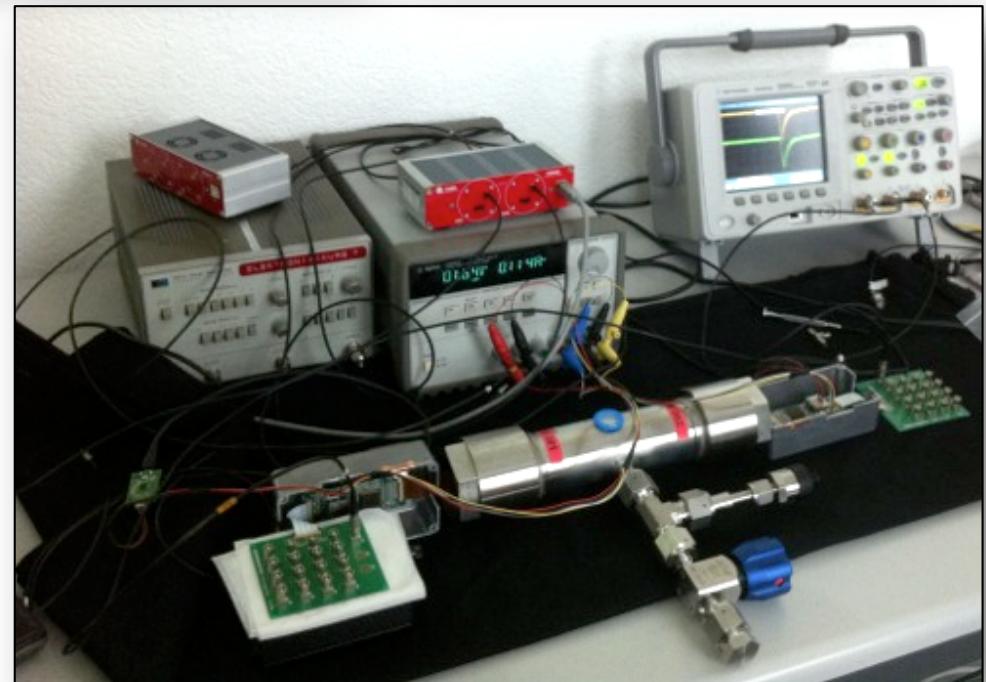
	Z	Photons/ MeV	Peak emission
^4He	2	15'000	70 nm
^{40}Ar	18	40'000	128 nm
^{131}Xe	54	46'000	175 nm
Nal(Tl)	11,53	40'000	415 nm

R. Chandra et al., 2012 JINST 7 C03035

SiPM and the proof of principle



- ▶ A short tube (19 cm) used for the proof of principle
- ▶ Filled with ${}^4\text{He}$ at 140 bar, an integrated wavelength shifter and two SiPMs mounted along the wall (by ARKTIS)
- ▶ Two SiPMs read-out through the Hamamatsu electronic board (C11206-0404FB)
- ▶ 2-channels 3-stage amplification with leading edge discrimination (SP5600A – CAEN)
- ▶ Digitizer with a sampling rate of 250 Ms/s 12 bit digitization (V720 – CAEN)



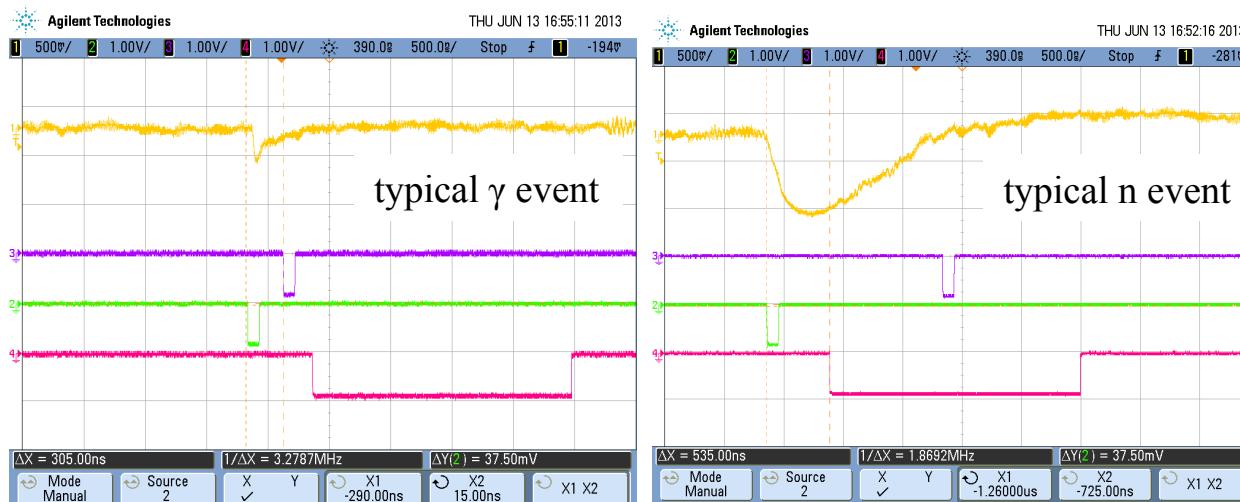
Counting measurements

Test performed measuring:

- Background, n and γ counting rate using ^{252}Cf and ^{60}Co source in contact

Two triggering scheme:

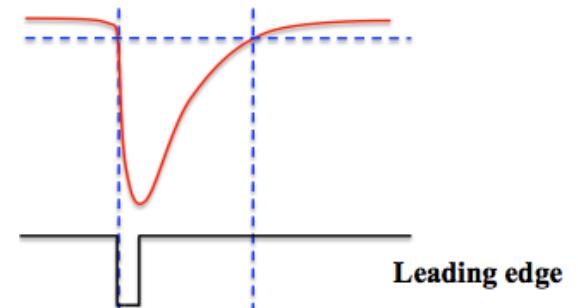
- Leading edge discrimination in coincidence
- Leading edge and delayed gate of each single SiPM in coincidence
 - Few parameters to be optimized:
 - Leading and trailing threshold
 - Delay time (ΔT)
 - Gate aperture



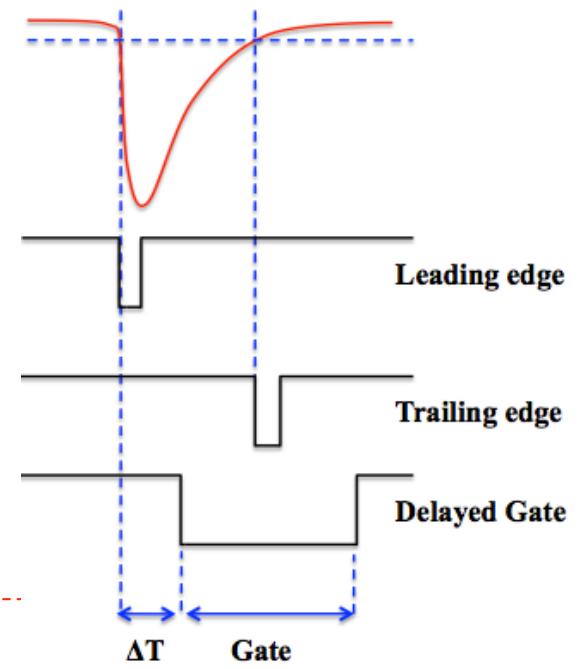
► R. Santoro

PhotoDet 2015, July 6-9, Moscow, Troitsk

1st Trigger Scheme



2nd Trigger Scheme



SiPM counting measurements

Result for the different trigger scheme @ 28°C

Counting rate [Hz]	no source	^{60}Co in contact	^{252}Cf in contact
Leading edge discrimination (Ch0 n Ch1) @31mV [Hz]	0.05	1.32	10.18
Delayed trigger, single detector [delay 700 ns, long gate 2 μs]	0.02	0.05	12.27
Delayed trigger, Ch0 n Ch1	0.01	0.01	8.61

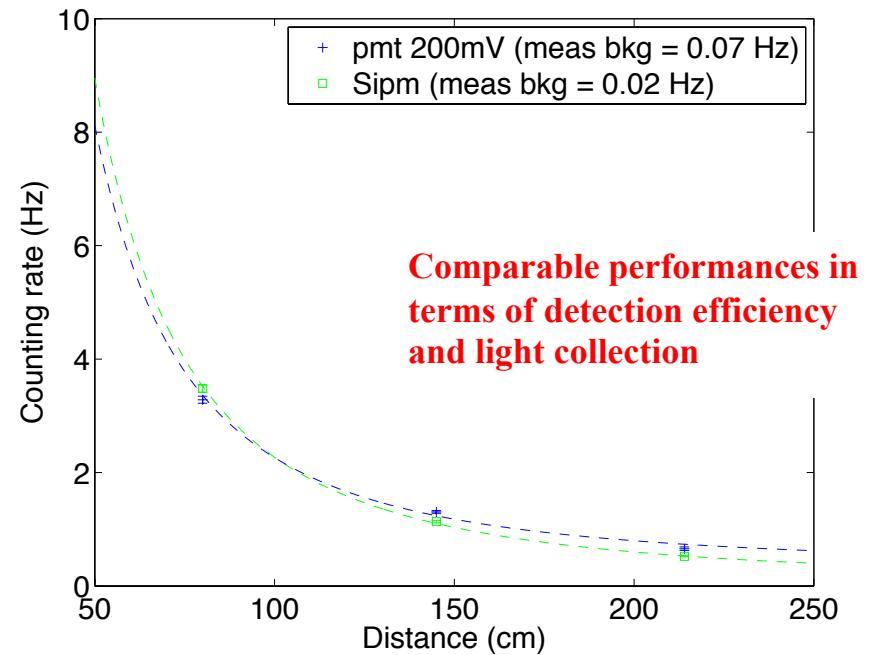
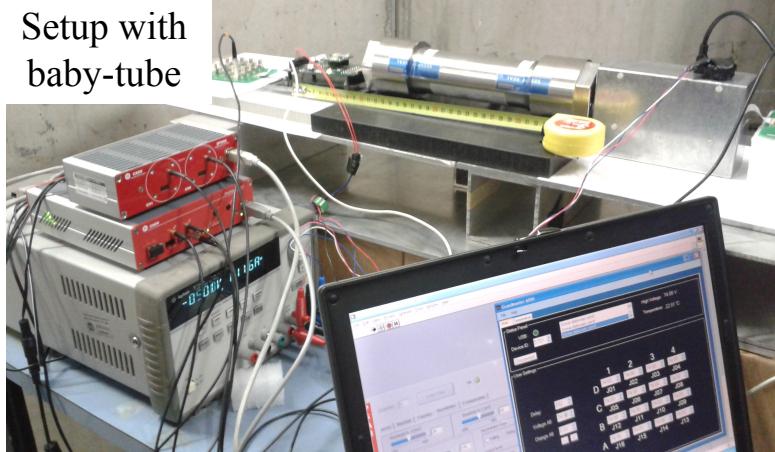
An amazing result, corresponding to a γ rejection power at the 10^6 level



[10 counts in 1000s, for a number of γ given by acceptance*activity*time
 $= 1/3 * 3 * 10^4 * 10^3 \sim 10^7$]

SiPM VS PMT counting measurements

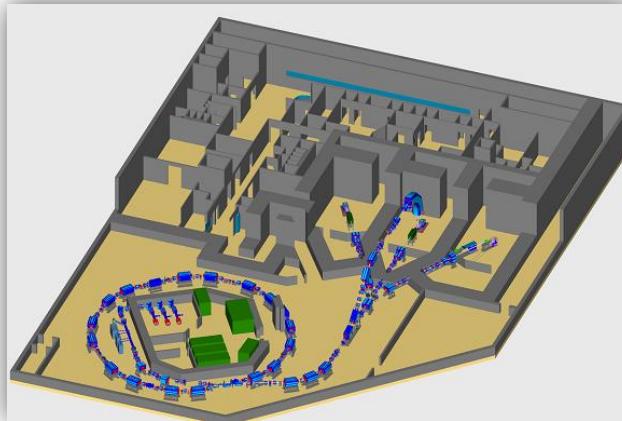
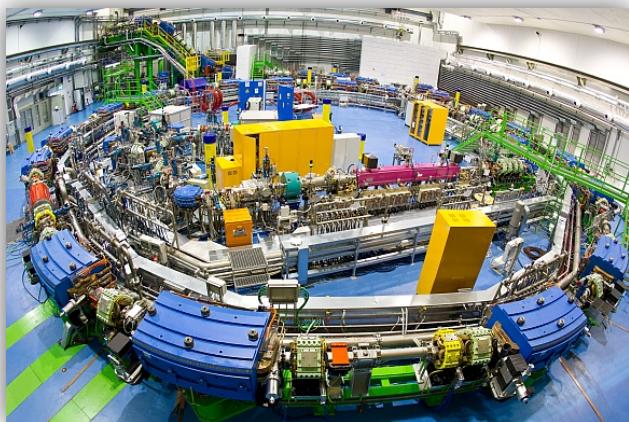
- ▶ Trigger: leading edge discrimination in coincidence among the 2 channels in the tube
 - ▶ Threshold set to have low bkg counting rate
 - ▶ No γ -rejection algorithm
 - ▶ Same strategy for both tubes
- ▶ The counting rate was measured at different distances from the ^{252}cf source



SiPM for beam profilometry @ CNAO



- ▶ Protons (250MeV) and carbon ions (4.8 GeV) beam
- ▶ Three treatments rooms

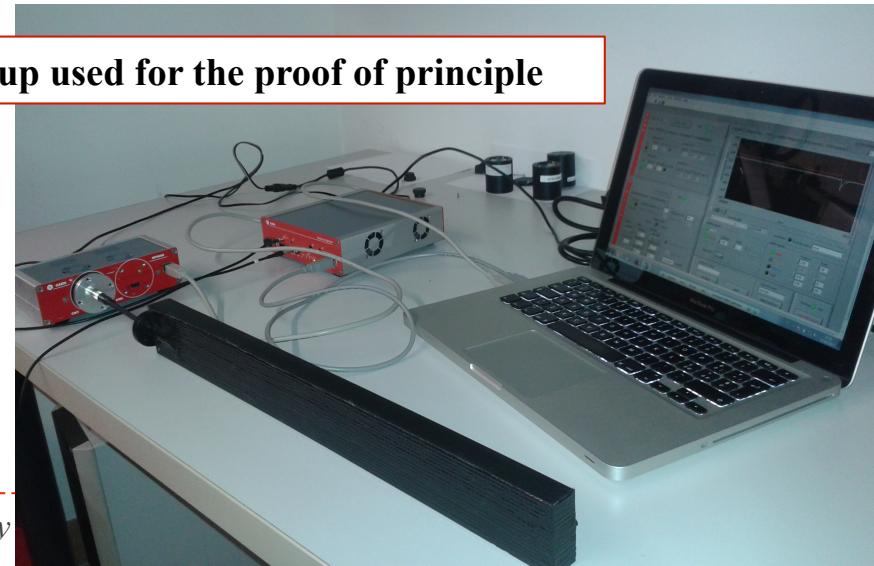


Measurement of the beam profile: wide dynamic range (\approx 4 order of magnitude)

- ▶ Scintillating fiber ($d=1\text{mm}$)
- ▶ SiPM ($1\times 1\text{mm}^2$)
- ▶ 1st stage amplification
- ▶ Digitizer for signal integration

▶ R. Santoro

PhotoDet 2015, July



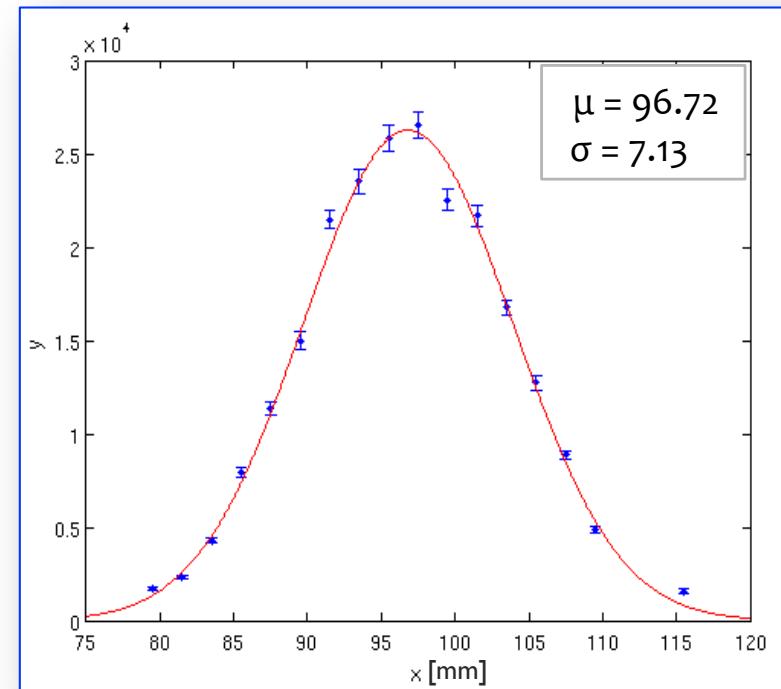
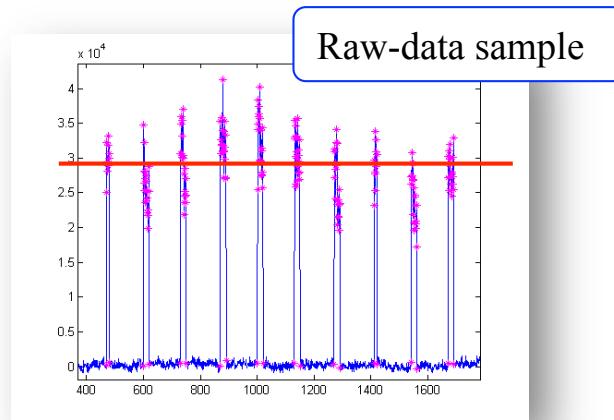
Beam profile

- ▶ Proton beam @ 117 MeV
- ▶ Intensity $\approx 2 \times 10^8$ / spill (1 sec long)
- ▶ duty cycle = 20%

Proof of principle

Two methods investigated:

1. Integration mode:
asynchronous long (\approx ms)
integration windows



σ and linearity are compatible with the ones measured with the film technique

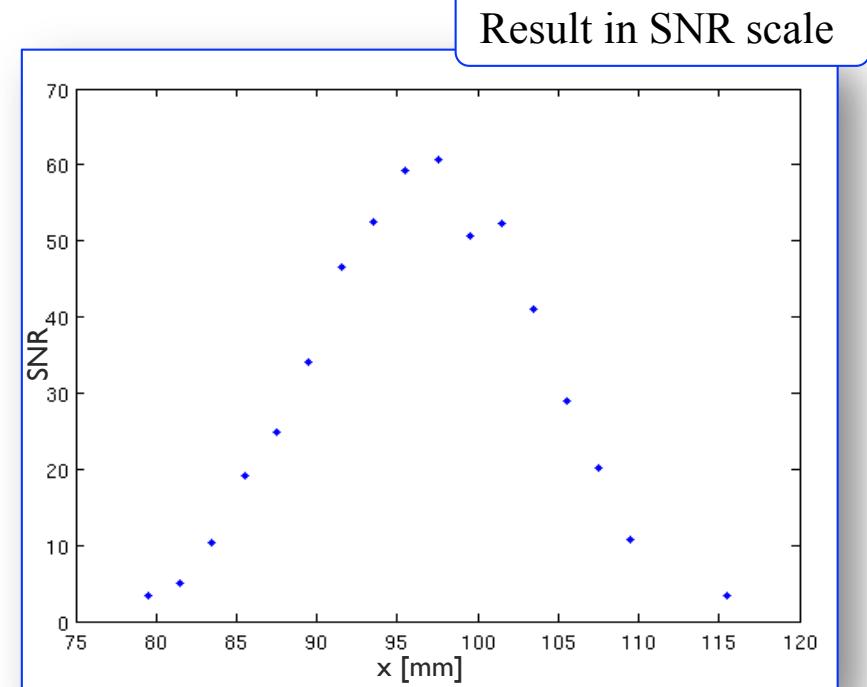
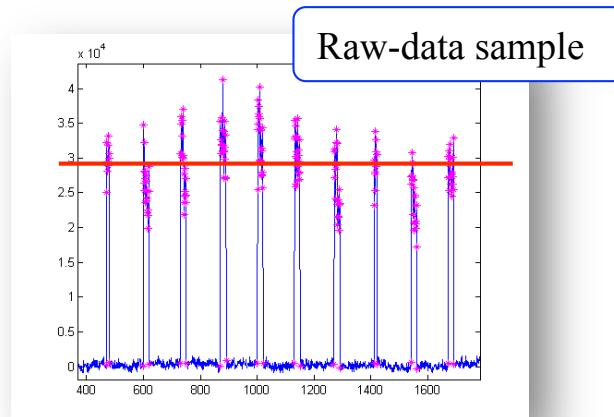
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Not enough dinamic range!

Beam profile

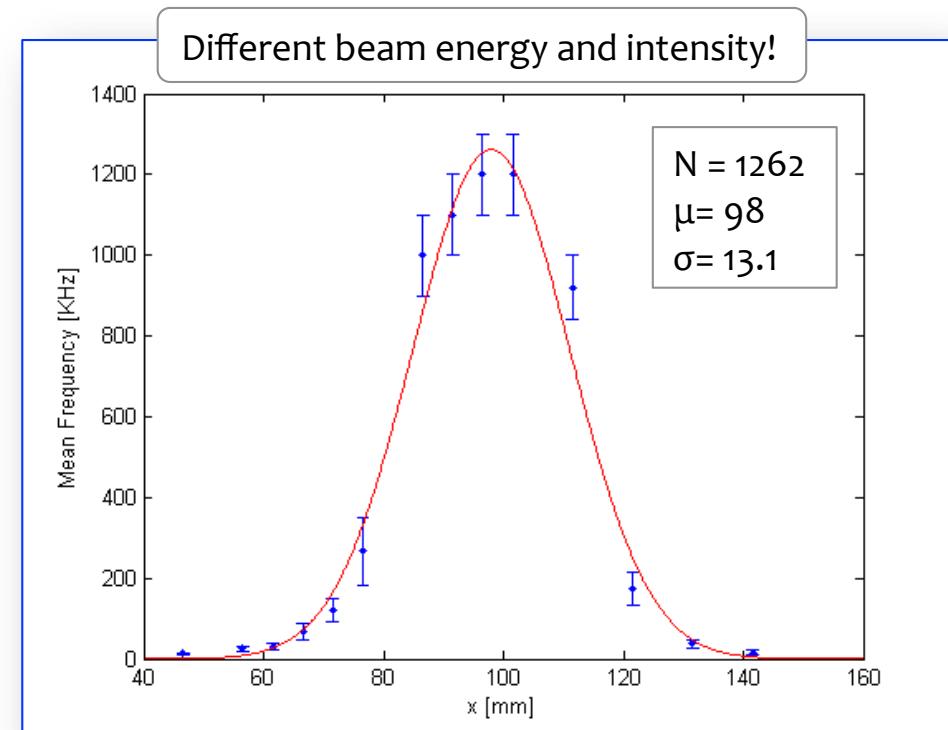
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2. Counting mode:
Leading-edge discrimination,
Threshold set to have DCR
@ Hz level

If were are not saturating
we get more than 4 orders
of magnitude



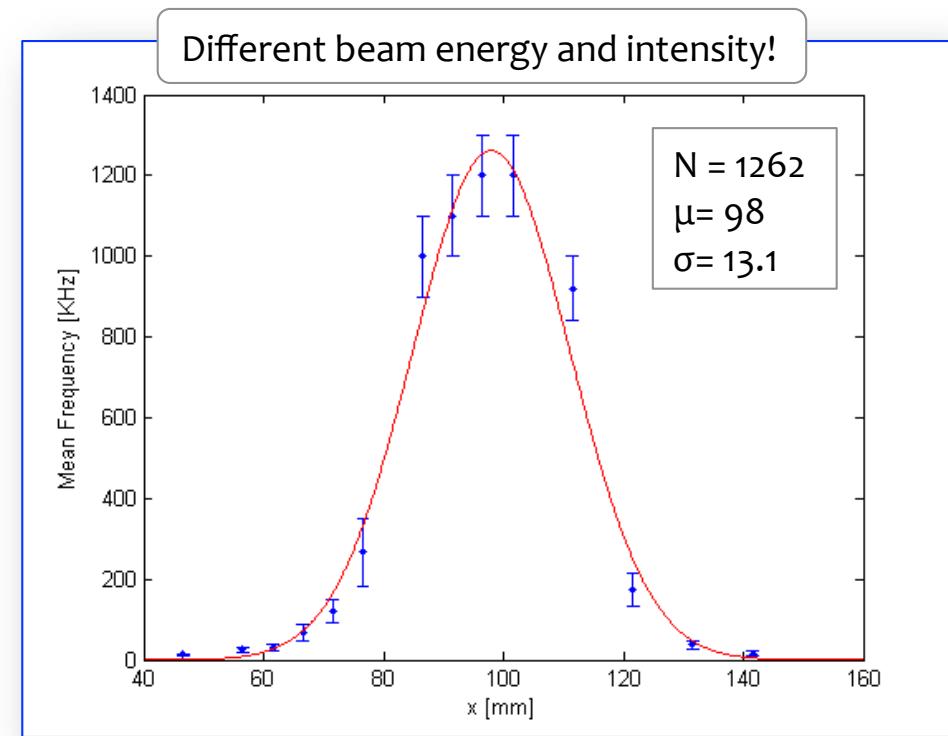
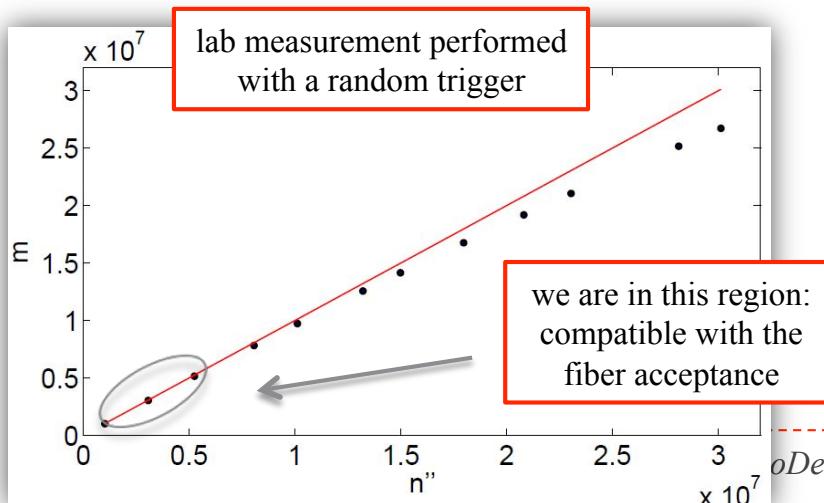
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Leading-edge discrimination,
Threshold set to have DCR
@ Hz level



Few personal considerations ...

- ▶ There is a growing interest for this new class of detector both in scientific & industrial communities
 - ▶ A good requirements definition and a deep knowledge of the detector characteristics could make the difference when exploring for new applications
 - ▶ Some times a simple and flexible setup plus a fast simulation may help in identifying the way to go

